

# High and Low Side Driver

#### **Features**

- Floating channel designed for bootstrap operation
- Fully operational to +600 V
- Tolerant to negative transient voltage
- dV/dt immune
- Gate drive supply range from 10 V to 20 V
- Undervoltage lockout for both channels
- 3.3 V and 5 V logic compatible
- Matched propagation delay for both channels
- Logic and power ground +/- 5 V offset
- Lower di/dt gate driver for better noise immunity
- RoHS compliant

# Output source/sink current 4 A / 4 A

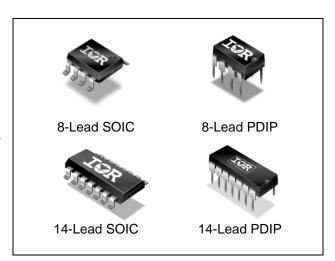
## **Description**

The IRS2186(4) are high voltage, high speed power MOSFET and IGBT drivers with independent high-side and low-side referenced output channels. Proprietary HVIC and latch immune CMOS technologies enable ruggedized monolithic construction. The logic input is compatible with standard CMOS or LSTTL output, down to 3.3 V logic. The output drivers feature a high pulse current buffer stage designed for minimum driver cross-conduction. The floating channel can be used to drive an N-channel power MOSFET or IGBT in the high-side configuration which operates up to 600 V.

#### **Product Summary**

V <sub>OFFSET</sub>	600 V
I <sub>O+/-</sub>	4 A / 4 A
V <sub>OUT</sub>	10 V – 20 V
Ton/off (typ.)	170 & 170 ns

### **Package Options**



## **Ordering Information**

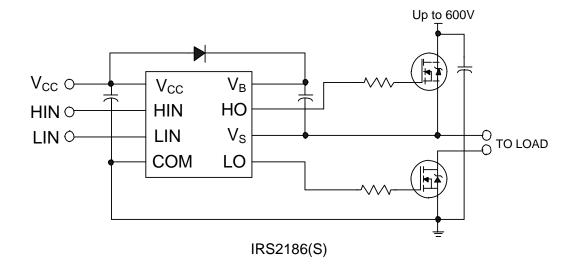
Daga Bart Normbar	Package Type	Standar	d Pack	Ondershie Deut Noumber	
Base Part Number	Base Part Number Package Type Form		Quantity	Orderable Part Number	
IRS2186SPBF	SO8N	Tube	95	IRS2186SPBF	
IRS2186SPBF	SO8N	Tape and Reel 2500		IRS2186STRPBF	
IRS21864SPBF	SO14N	Tube	55	IRS21864SPBF	
IRS21864SPBF	SO14N	Tape and Reel	2500	IRS21864STRPBF	
IRS2186PBF	PDIP8	Tube	50	IRS2186PBF	
IRS21864PBF	PDIP14	Tube	25	IRS21864PBF	

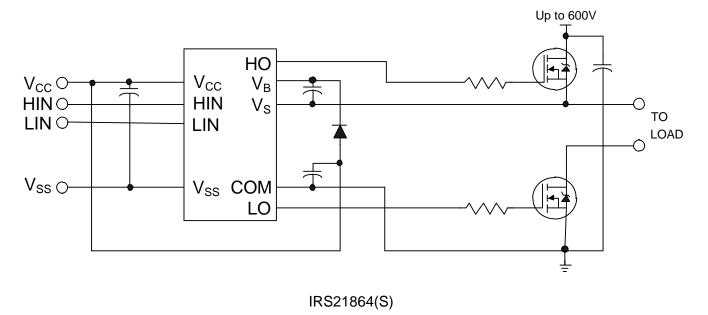


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# **Typical Connection Diagram**





(Refer to Lead Assignments for correct pin configuration). These diagrams show electrical connections only. Please refer to our Application Notes and Design Tips for proper circuit board layout.



#### **Absolute Maximum Ratings**

Absolute maximum ratings indicate sustained limits beyond which damage to the device may occur. All voltage parameters are absolute voltages referenced to COM. The thermal resistance and power dissipation ratings are measured under board mounted and still air conditions.

Symbol	Definition	Min.	Max.	Units	
V <sub>B</sub>	High side floating absolute voltage		-0.3	620 <sup>†</sup>	
Vs	High side floating supply offset voltage	е	V <sub>B</sub> - 20	V <sub>B</sub> + 0.3	
V <sub>HO</sub>	High side floating output voltage		V <sub>S</sub> - 0.3	V <sub>B</sub> + 0.3	
V <sub>CC</sub>	Low side and logic fixed supply voltage	ge	-0.3	20 <sup>†</sup>	V
$V_{LO}$	Low side output voltage		-0.3	V <sub>CC</sub> + 0.3	
V <sub>IN</sub>	Logic input voltage (HIN & LIN)		V <sub>SS</sub> - 0.3	V <sub>CC</sub> + 0.3	
V <sub>SS</sub>	Logic ground (IRS21864)		V <sub>CC</sub> - 20	V <sub>CC</sub> + 0.3	
dV <sub>S</sub> /dt	Allowable offset supply voltage transi	Allowable offset supply voltage transient			V/ns
		8 lead PDIP	_	1	
5	Package power dissipation	8 lead SOIC	_	0.625	100
$P_{D}$	@ T <sub>A</sub> ≤ +25°C	14 lead PDIP	_	1.6	- W
		14 lead SOIC	_	1	
		8 lead PDIP	_	125	
Dul	Thermal resistance, junction to	8 lead SOIC	_	200	] °C/W
Rth <sub>JA</sub>	Rth <sub>JA</sub> ambient	14 lead PDIP	_	75	7 0, 11
		14 lead SOIC	_	120	
TJ	Junction temperature		_	150	
T <sub>S</sub>	Storage temperature		-50	150	°C
TL	Lead temperature (soldering, 10 second	onds)	_	300	7

## **Recommended Operating Conditions**

The input/output logic timing diagram is shown in figure 1. For proper operation the device should be used within the recommended conditions. The  $V_S$  and  $V_{SS}$  offset rating is tested with all supplies biased at 15 V differential.

Symbol	Definition	Min.	Max.	Units
V <sub>B</sub>	High side floating absolute voltage	V <sub>S</sub> + 10	V <sub>S</sub> + 20	
Vs	High side floating supply offset voltage	††	600	
$V_{HO}$	High side floating output voltage	Vs	$V_{B}$	
Vcc	Low side and logic fixed supply voltage	10	20	V
$V_{LO}$	Low side output voltage	0	V <sub>CC</sub>	
$V_{IN}$	Logic input voltage (HIN & LIN)	V <sub>SS</sub>	V <sub>CC</sub>	
$V_{SS}$	Logic ground (IRS21864)	-5	5	
$T_A$	Ambient temperature	-40	125	°C

<sup>†</sup> All supplies are fully tested at 25 V and an internal 20 V clamp exists for each supply

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<sup>11</sup> Logic operational for  $V_S$  of -5 V to 600 V. Logic state held for  $V_S$  of -5 V to  $-V_{BS}$  (Please refer to the Design Tip DT97-3 for more details)



### **Dynamic Electrical Characteristics**

 $V_{BIAS}$  (V<sub>CC</sub>, V<sub>BS</sub>) = 15 V, V<sub>SS</sub> = COM, C<sub>L</sub> = 1000 pF and T<sub>A</sub> = 25 °C unless otherwise specified.

Symbol	Definition	Min.	Тур.	Max.	Units	Test Conditions
t <sub>on</sub>	Turn-on propagation delay	_	170	250		$V_S = 0 V$
t <sub>off</sub>	Turn-off propagation delay	_	170	250		V <sub>S</sub> = 0 V or 600 V
t <sub>r</sub>	Turn-on rise time	_	22	38	ns	V 0.V
t <sub>f</sub>	Turn-off fall time	_	18	30		V <sub>S</sub> = 0 V
MT	Delay matching, HS & LS turn on/off	_	0	35		

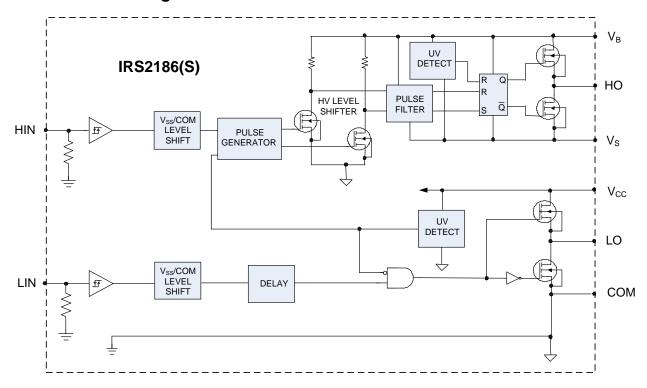
#### **Static Electrical Characteristics**

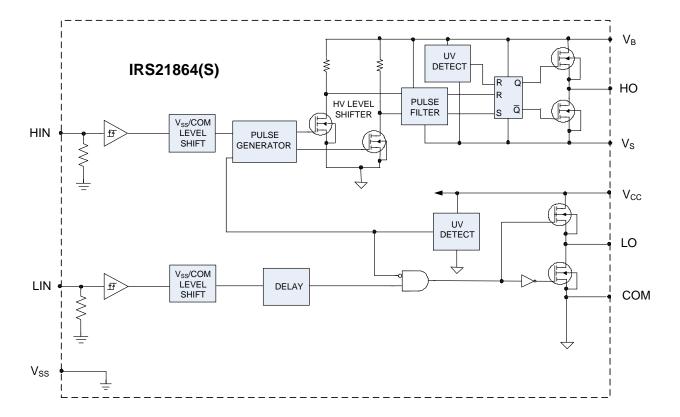
V<sub>BIAS</sub> (V<sub>CC</sub>, V<sub>BS</sub>) = 15 V, V<sub>SS</sub> = COM, and T<sub>A</sub> = 25 °C unless otherwise specified. The V<sub>IL</sub>, V<sub>IH</sub>, and I<sub>IN</sub> parameters are referenced to V<sub>SS</sub>/COM and are applicable to the respective input leads HIN and LIN. The V<sub>O</sub>, I<sub>O</sub>, and RON parameters are referenced to COM and are applicable to the respective output leads: HO and LO.

Symbol	Definition	Min.	Тур.	Max.	Units	Test Conditions
$V_{IH}$	Logic "1" input voltage	2.5	1	l		V <sub>CC</sub> = 10 V to 20 V
$V_{IL}$	Logic "0" input voltage	—		0.8	V	ACC = 10 A 10 50 A
V <sub>OH</sub>	High level output voltage, $V_{BIAS}$ - $V_{O}$	—		1.4	V	$I_O = 0 A$
$V_{OL}$	Low level output voltage, VO		_	0.15		$I_O = 20 \text{ mA}$
$I_{LK}$	Offset supply leakage current	—		50		$V_B = V_S = 600 \text{ V}$
I <sub>QBS</sub>	Quiescent V <sub>BS</sub> supply current	20	60	150		V <sub>IN</sub> = 0 V or 5 V
IQCC	Quiescent V <sub>CC</sub> supply current	50	120	240	μA	VIN = 0 V 01 2 V
I <sub>IN+</sub>	Logic "1" input bias current	_	25	60		V <sub>IN</sub> = 5 V
I <sub>IN-</sub>	Logic "0" input bias current	_	1	5		$V_{IN} = 0 V$
V <sub>CCUV+</sub>	V <sub>CC</sub> and V <sub>BS</sub> supply undervoltage	8	8.9	9.8		
V <sub>BSUV+</sub>	positive going threshold	0	0.0	0.0		
V <sub>CCUV</sub> -	$V_{CC}$ and $V_{BS}$ supply undervoltage	7.4	8.2	9	V	
V <sub>BSUV</sub> -	negative going threshold		0.2			
V <sub>CCUVH</sub>	Hysteresis	0.3	0.7	_		
V <sub>BSUVH</sub>	,					
I <sub>O+</sub>	Output high short circuit pulsed	2	4	_		$V_O = 0 V$ ,
10+	current	_	•		Α	PW ≤ 10 µs
I <sub>O-</sub>	Output low short circuit pulsed	2	4	_		$V_0 = 15 V$ ,
.0-	current					PW ≤ 10 µs



## **Functional Block Diagram**



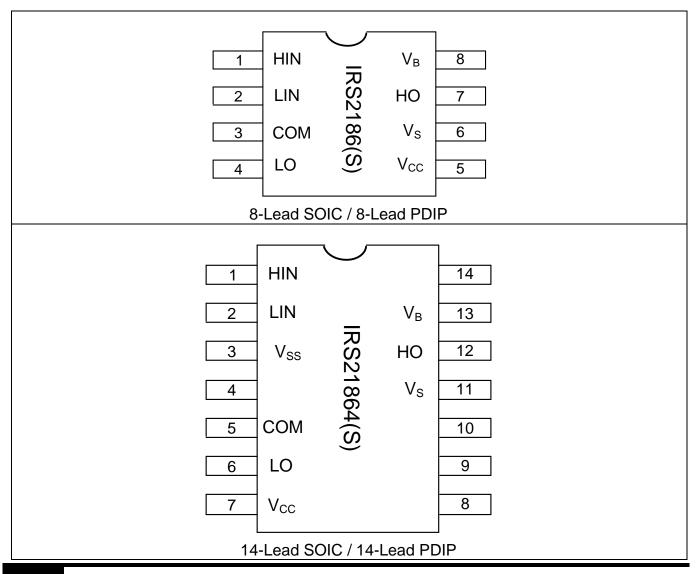




#### **Lead Definitions**

Symbol	Description
HIN	Logic input for high side gate driver output (HO), in phase
LIN	Logic input for low side gate driver output (LO), in phase
$V_{SS}$	Logic ground (IRS21864)
V <sub>B</sub>	High side floating supply
НО	High side gate drive output
Vs	High side floating supply return
V <sub>C</sub> C	Low side and logic fixed supply
LO	Low side gate drive output
COM	Low side return

## **Lead Assignments**





# **Application Information and Additional Details**

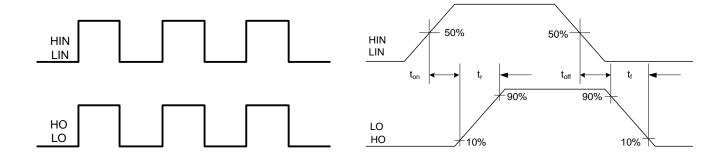


Figure 1. Input/Output Timing Diagram

Figure 2. Switching Time Waveform Definitions

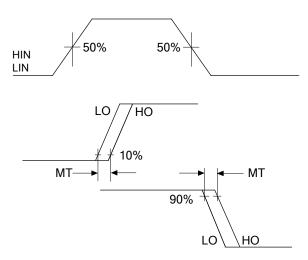
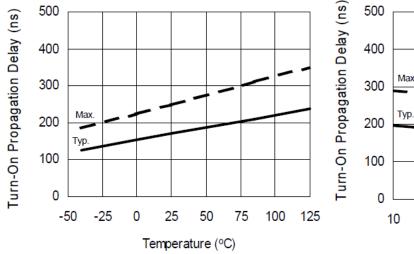


Figure 3. Delay Matching Waveform Definitions





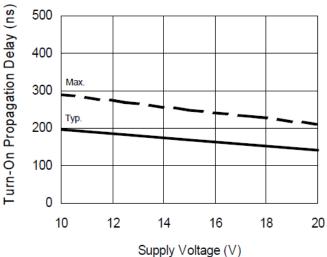
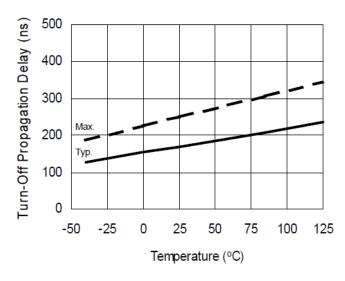


Figure 4A. Turn-On Propagation Delay vs. **Temperature** 

Figure 4B. Turn-on Propagation Delay vs. Supply Voltage



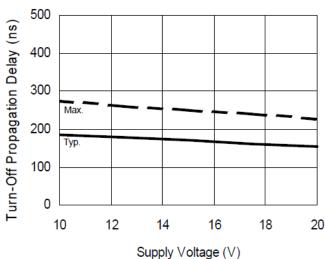
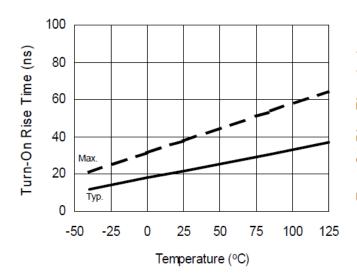
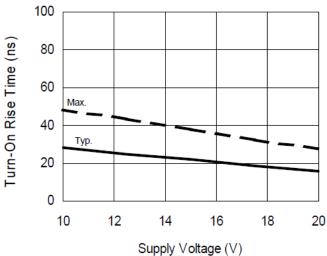


Figure 5A. Turn-Off Propagation Delay vs. **Temperature** 

Figure 5B. Turn-Off Propagation Delay vs. Supply Voltage

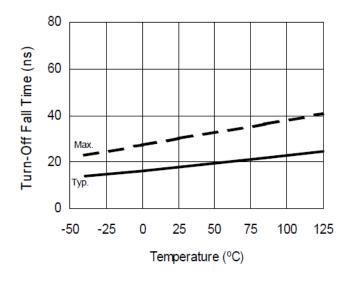






6A. Turn-On Rise Time vs. Temperature

Figure 6B. Turn-On Rise Time vs. Supply Voltage



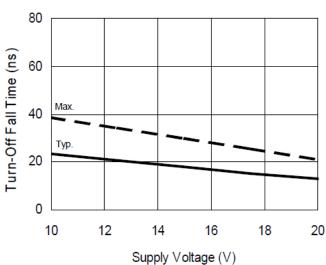
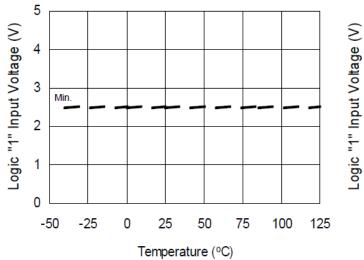


Figure 7A. Turn-Off Fall Time vs. Temperature

Figure 7B. Turn-Off Fall Time vs. Supply Voltage





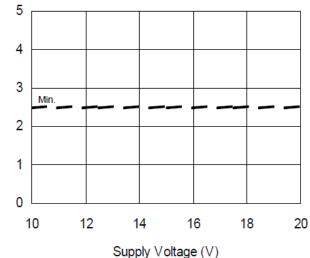
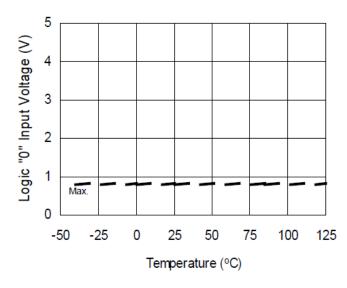


Figure 8A. Logic "1" Input Voltage vs. Temperature

Figure 8B. Logic "1" Input Voltage vs. Supply Voltage



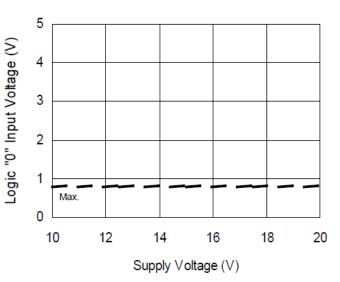
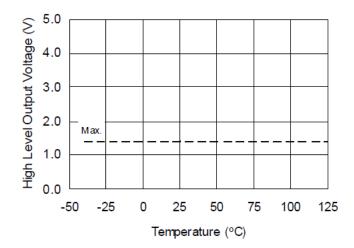


Figure 9A. Logic "0" Input Voltage vs. Temperature

Figure 9B. Logic "0" Input Voltage vs. Supply Voltage





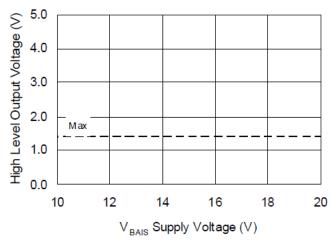
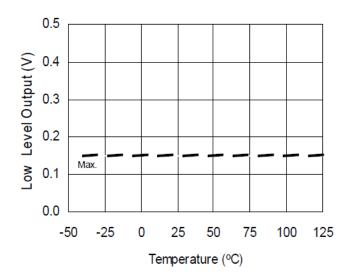


Figure 10A. High Level Output Voltage vs. Temperature (Io = 0mA)

Figure 10B. High Level Output Voltage vs. Supply Voltage (Io = 0mA)



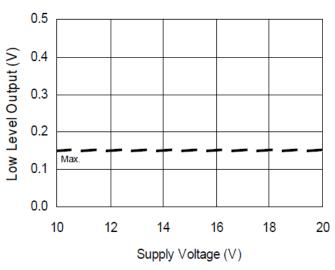
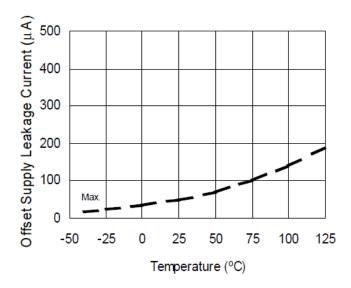


Figure 11A. Low Level Output vs. Temperature

Figure 11B. Low Level Output vs. Supply Voltage





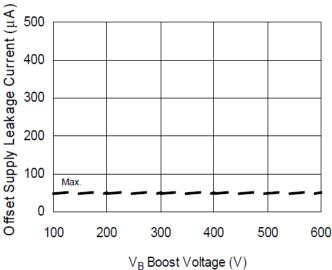
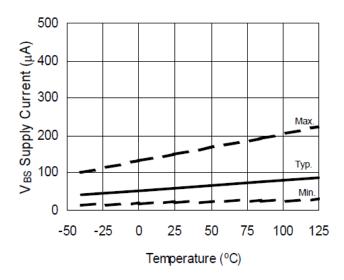


Figure 12A. Offset Supply Leakage Current

Figure 12B. Offset Supply Leakage Current vs. V<sub>B</sub> **Boost Voltage** 



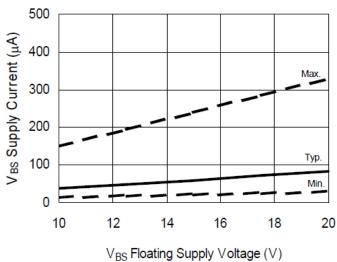
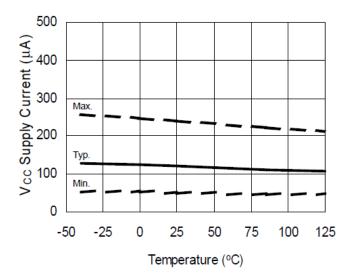


Figure 13A. V<sub>BS</sub> Supply Current vs. Temperature

Figure 13B. V<sub>BS</sub> Supply Current vs. V<sub>BS</sub> Floating **Supply Voltage** 





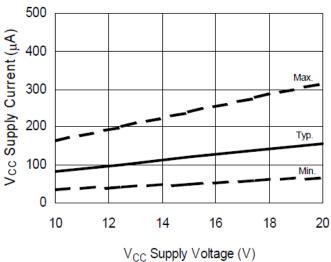
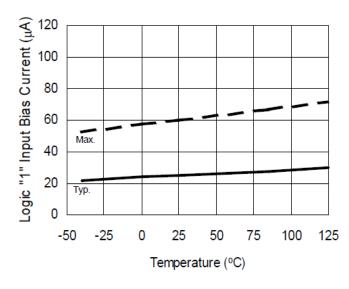


Figure 14A. V<sub>CC</sub> Supply Current vs. Temperature

Figure 14B. V<sub>CC</sub> Supply Current vs. Supply Voltage



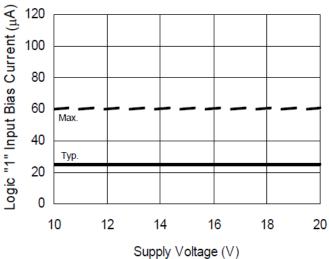
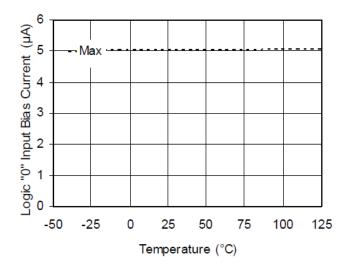


Figure 15A. Logic "1" Input Bias Current vs.
Temperature

Figure 15B. Logic "1" Input Bias Current vs. Supply Voltage





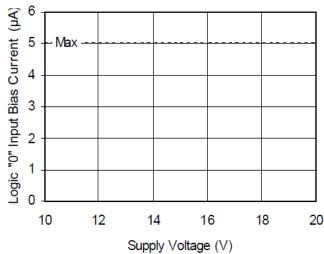
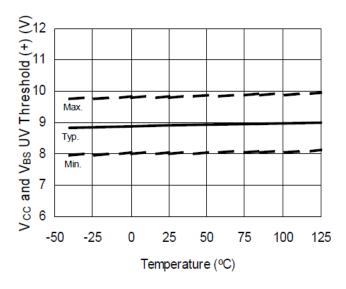


Figure 16A. Logic "0" Input Bias Current vs. **Temperature** 

Figure 16B. Logic "0" Input Bias Current vs. Voltage



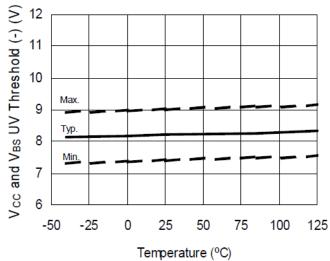
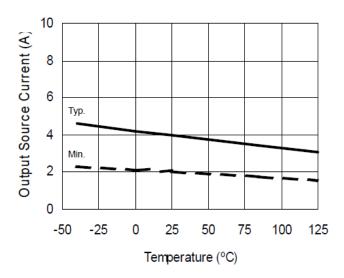


Figure 17. V<sub>CC</sub> and V<sub>BS</sub> Undervoltage Threshold (+) vs. Temperature

Figure 18. V<sub>CC</sub> and V<sub>BS</sub> Undervoltage Threshold (-) vs. Temperature





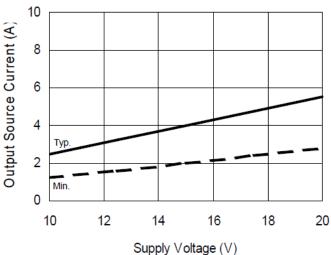
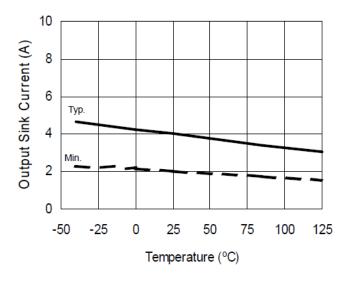


Figure 19A. Output Source Current vs. Temperature

Figure 19B. Output Source Current vs. Supply Voltage



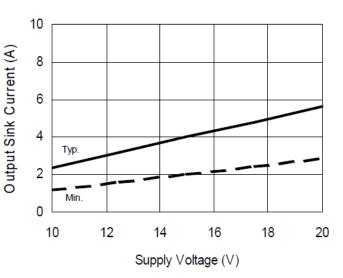
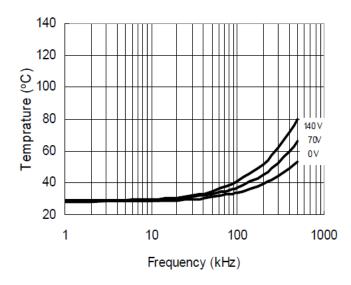


Figure 20A. Output Sink Current vs. Temperature

Figure 10B. Output Sink Current vs. Supply Voltage





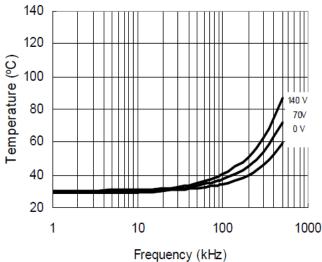
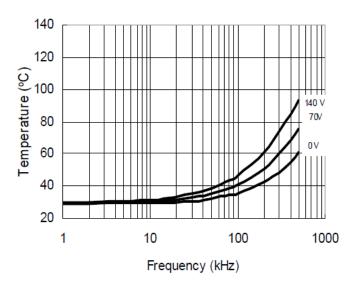


Figure 21. IRS2186 vs. Frequency (IRFBC20)  $R_{\text{gate}} = 33\Omega$ ,  $V_{\text{CC}} = 15V$ 

Figure 22. IRS2186 vs. Frequency (IRFBC30)  $R_{gate} = 22\Omega$ ,  $V_{CC} = 15V$ 



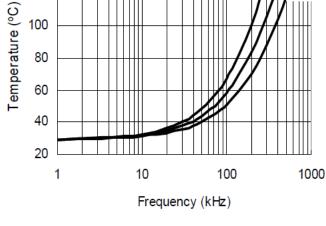


Figure 23. IRS2186 vs. Frequency (IRFBC40)  $R_{gate} = 15\Omega$ ,  $V_{CC} = 15V$ 

Figure 24. IRS2186 vs. Frequency (IRFPE50)  $R_{gate} = 10\Omega$ ,  $V_{CC} = 15V$ 

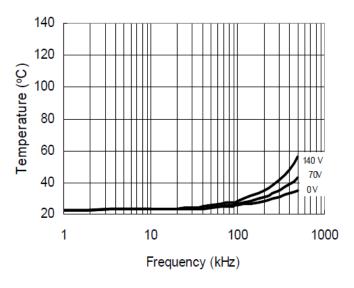
140 V

140

120

100





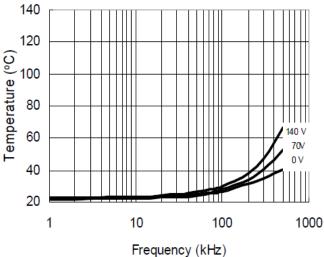
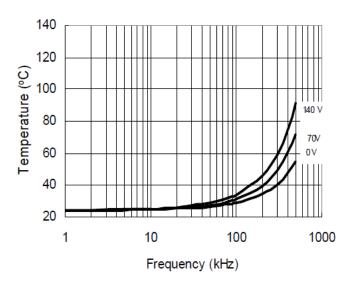


Figure 25. IRS21864 vs. Frequency (IRFBC20)  $R_{gate} = 33\Omega$ ,  $V_{CC} = 15V$ 

Figure 26. IRS21864 vs. Frequency (IRFBC30)  $R_{gate} = 22\Omega$ ,  $V_{CC} = 15V$ 



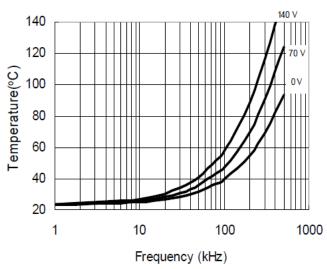
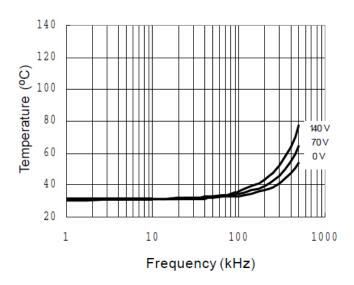


Figure 27. IRS21864 vs. Frequency (IRFBC40)  $R_{gate} = 15\Omega$ ,  $V_{CC} = 15V$ 

Figure 28. IRS21864 vs. Frequency (IRFPE50)  $R_{gate} = 10\Omega$ ,  $V_{CC} = 15V$ 





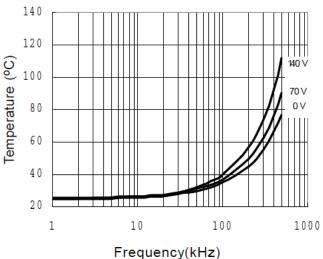
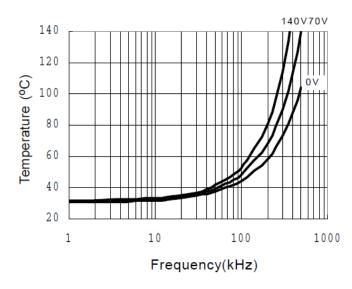


Figure 29. IRS2186S vs. Frequency (IRFBC20)  $R_{gate} = 33\Omega$ ,  $V_{CC} = 15V$ 

Figure 30. IRS2186S vs. Frequency (IRFBC30)  $R_{gate} = 22\Omega$ ,  $V_{CC} = 15V$ 



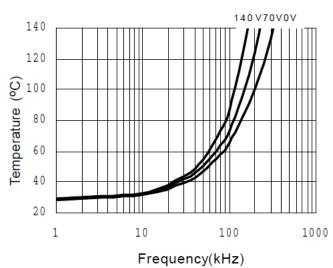
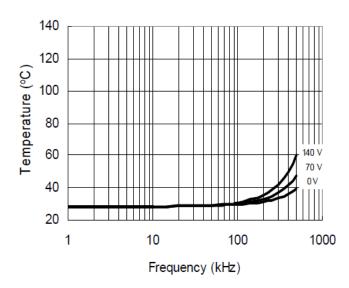


Figure 31. IRS2186S vs. Frequency (IRFBC40)  $R_{gate} = 15\Omega$ ,  $V_{CC} = 15V$ 

Figure 32. IRS2186S vs. Frequency (IRFPE50)  $R_{\text{gate}} = 10\Omega$ ,  $V_{\text{CC}} = 15V$ 





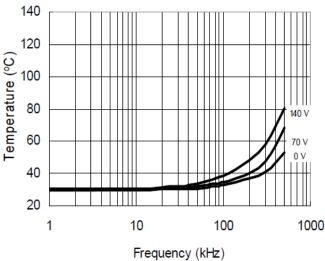
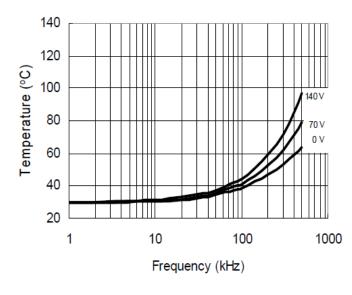


Figure 33. IRS21864S vs. Frequency (IRFBC20)  $R_{gate}$  = 33 $\Omega$ ,  $V_{CC}$  = 15V

Figure 34. IRS21864S vs. Frequency (IRFBC30)  $R_{\text{gate}} = 22\Omega$ ,  $V_{\text{CC}} = 15V$ 



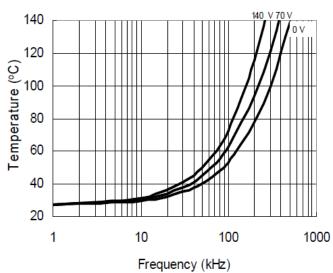
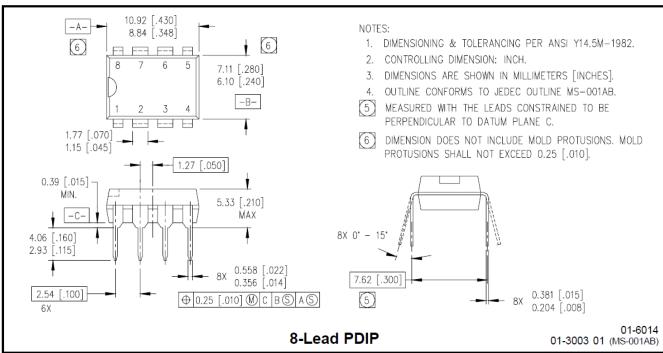


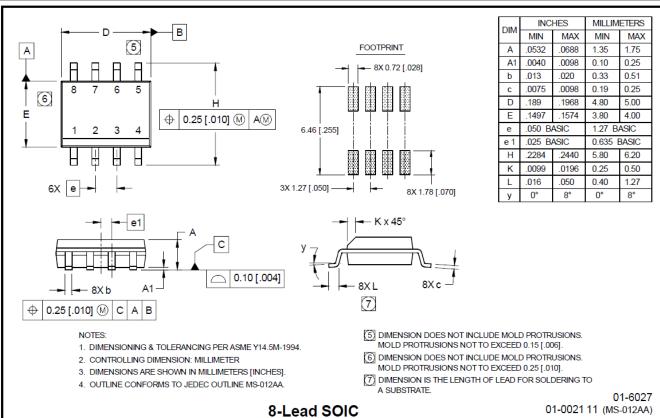
Figure 35. IRS21864S vs. Frequency (IRFBC40)  $R_{gate}$  = 15 $\Omega$ ,  $V_{CC}$  = 15V

Figure 36. IRS21864S vs. Frequency (IRFPE50)  $R_{gate}$  = 10 $\Omega$ ,  $V_{CC}$  = 15V



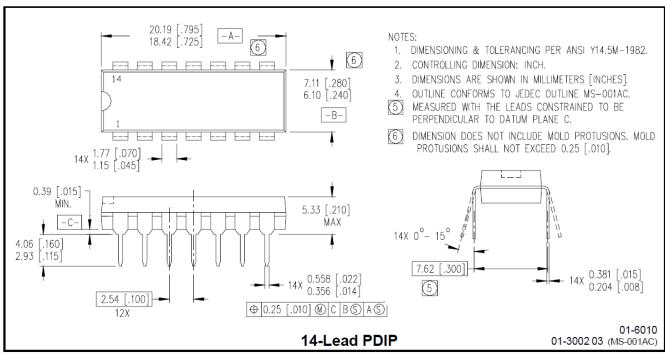
#### Package Details: PDIP8, SO8N

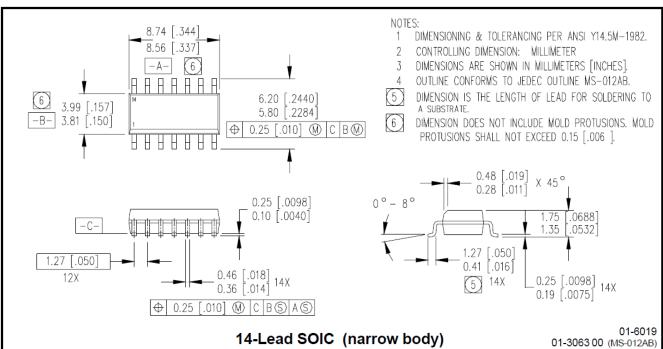






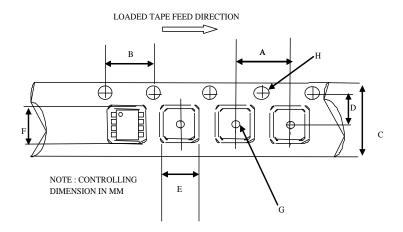
#### Package Details: PDIP14, SO14N





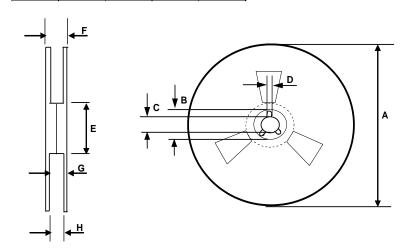


## Tape and Reel Details: SO8N



#### CARRIER TAPE DIMENSION FOR 8SOICN

	Metric		Imp	erial
Code	Min	Max	Min	Max
Α	7.90	8.10	0.311	0.318
В	3.90	4.10	0.153	0.161
С	11.70	12.30	0.46	0.484
D	5.45	5.55	0.214	0.218
E	6.30	6.50	0.248	0.255
F	5.10	5.30	0.200	0.208
G	1.50	n/a	0.059	n/a
Н	1.50	1.60	0.059	0.062

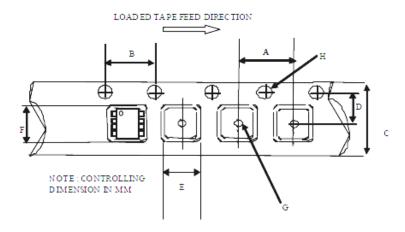


#### REEL DIMENSIONS FOR 8SOICN

	Metric		Imp	erial
Code	Min	Max	Min	Max
Α	329.60	330.25	12.976	13.001
В	20.95	21.45	0.824	0.844
С	12.80	13.20	0.503	0.519
D	1.95	2.45	0.767	0.096
E F	98.00	102.00	3.858	4.015
	n/a	18.40	n/a	0.724
G	14.50	17.10	0.570	0.673
Н	12.40	14.40	0.488	0.566

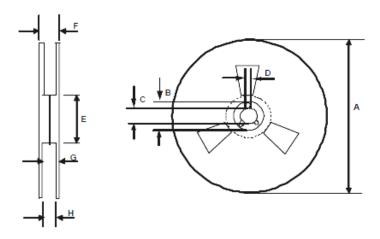


## **Tape and Reel Details: SO14N**



CARRIER TAPE DIMENSION FOR 14 SOICN

OARTHER	TATE DIME	THOTON TO	14 14001011	
	M etric		lm p	erial
Code	Min	Max	M in	Max
Α	7.90	8.10	0.311	0.318
B 3	.90	4.10	0.153	0.161
O	15.70	16.30	0.618	0.641
D	7.40	7.60	0.291	0.299
E	6.40	6.60	0.252	0.260
F	9.40	9.60	0.370	0.378
G	1.50	n/a	0.059	n/a
Н	1.50	1.60	0.059	0.062

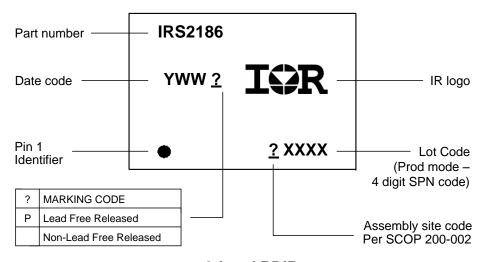


REEL DMENSIONS FOR 14 SOICN

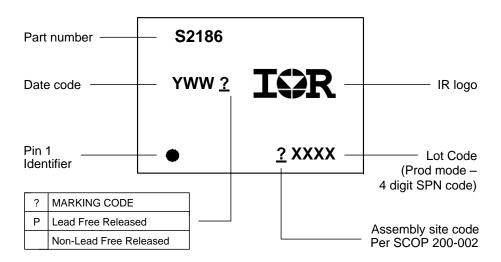
	M etric		Im p	erial
Code	Min	Max	M in	Max
A	329.60	330.25	12.976	13.001
В	20.95	21.45	0.824	0.844
C D	12.80	13.20	0.503	0.519
D	1.95	2.45	0.767	0.096
E	98.00	102.00	3.858	4.015
F	n/a	22.40	n/a	0.881
G	18.50	21.10	0.728	0.830
G H	16.40	18.40	0.645	0.724



## **Part Marking Information**

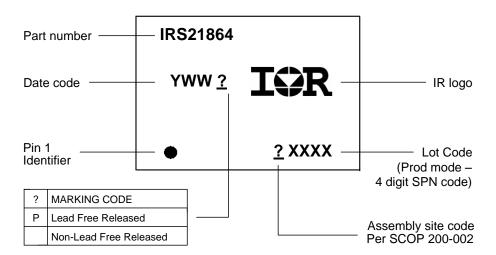


8-Lead PDIP

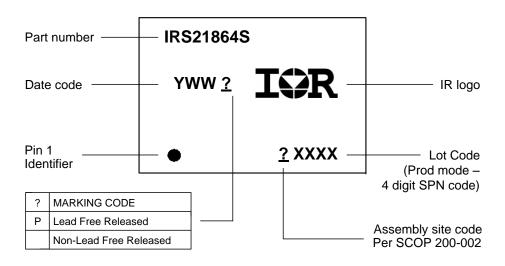


8-Lead SOIC





14-Lead PDIP



14-Lead SOIC



### Qualification Information<sup>†</sup>

Qualification Level		Industrial <sup>††</sup> (per JEDEC JESD 47)	
	Industrial qualification.	Comments: This family of ICs has passed JEDEC's Industrial qualification. IR's Consumer qualification level is granted by extension of the higher Industrial level.	
Moisture Sensitivity Level	SOIC8N	MSL2 <sup>†††</sup> (per IPC/JEDEC J-STD 020)	
	PDIP8	Not applicable (non-surface mount package style)	
	SOIC14N	MSL2 <sup>†††</sup> (per IPC/JEDEC J-STD 020)	
	PDIP14	Not applicable (non-surface mount package style)	
RoHS Compliant		Yes	

- † Qualification standards can be found at International Rectifier's web site <a href="http://www.irf.com/">http://www.irf.com/</a>
- †† Higher qualification ratings may be available should the user have such requirements. Please contact your International Rectifier sales representative for further information.
- ††† Higher MSL ratings may be available for the specific package types listed here. Please contact your International Rectifier sales representative for further information.

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